



MBRB30100CT thru MBRB30200CT

30.0A Schottky Barrier Rectifiers

Rectifier Reverse Voltage 100 to 200V

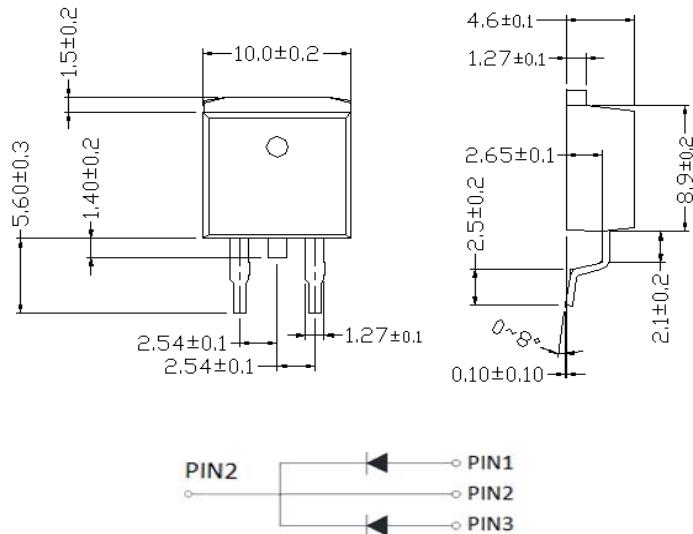
TO-263

Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 260 °C max. 8 s, per JESD 22-B106

Mechanical Data

- **Package:** TO-220AB
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



Dimensions in millimeters (1mm =0.0394")

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRB30100CT	MBRB30150CT	MBRB30200CT
Device marking code			MBRB30100CT	MBRB30150CT	MBRB30200CT
Repetitive Peak Reverse Voltage	V _{RRM}	V	100	150	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	I _O	A		30	
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25°C	I _{FSM}	A		180	
Current Squared Time @1ms≤t<8.3ms T _j =25°C,	I ² t	A ² s		134	
Storage Temperature	T _{stg}	°C		-55 ~ +175	
Junction Temperature	T _j	°C		-55 ~ +150	

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRB30100CT	MBRB30150CT	MBRB30200CT
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =15.0A	0.87	0.93	0.95
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	VRM=V _{RRM} Ta=25°C	0.15	20	0.1
	I _{RRM2}		VRM=V _{RRM} Ta=125°C			
Thermal Resistance	Between junction and case		R _{θJ-C} °C/W		2.0	

Rating and Characteristic Curves ($T_A=25^\circ\text{C}$ Unless otherwise noted)

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